# DATA REDUCTION AND ANALYSIS-EXPERIMENTAL IEMP/SGEMP ELECTRON BEAM STUDY, FIRST INTERM REPORT: 40 KEV BEAM ENERGY

Kaman Sciences Corporation P.O. Box 7463 Colorado Springs, Colorado 80933 December 1975

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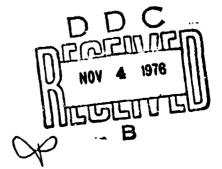
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#### 20. ABSTRACT (Continued)

Details of the experimental apparatus and techniques are found in the following reference: "A Study of IEMP/SGEMP Phenomenology Using Electron Beam Simulation;" also, additional discussion is presented in Appendix B in this report. Additional similar interim reports will cover the remaining two sets of data comprising the nominal 60 keV mean-energy beam into the 18 cm length chamber and nominal 125 keV beam into the 30 cm length chamber.

A final report will contain analyses and correlation of the tree data sets covered in the interim reports as well as the 60 keV data set previously reduced and reported on in the above-mentioned reference. The final report will also contain results of computer calculations using Kaman Sciences' two-dimensional code EBBTIDE for comparison with appropriate determined quantities.

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### PREFACE

The bulk of the data processing techniques and codes employed in reducing the data presented in this report were developed under the leadership of Dr. J. S. Duval prior to his leaving Kaman Sciences to join the U. S. Geological Survey. Additional discussions with him during the course of the work presented herein are also acknowledged with pleasure.

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DATA REDUCTION AND ANALYSIS-EXPERIMENTAL IEMP/SGEMP ELECTRON BEAM STUDY, FIRST INTERIM REPORT: 40 keV BEAM ENERGY

## I. INTRODUCTION

The following report is Kaman Sciences' first formal interim report to the Defense Nuclear Agency on work supported under contract number DNA001-75-C-0167. Presented herein are reduced data from the series of internal electromagnetic pulse (IEMP) simulation experiments carried out under sponsorship of the Ballistic Missile Defense System Command, contract number DASG60-74-C-0015, early in 1974.

The experiments carried out were designed to explore under controlled laboratory conditions the phenomenology governing the behavior of a uniformly distributed beam of electrons injected axially into a test chamber of cylindrical geometry and to provide a reliable body of experimental data against which to evaluate existing or evolving system generated electromagnetic pulse (SGEMP) computational codes.

The cylindrical experimental chamber was instrumented in such a manner as to provide correlated time history data on transmitted currents as a function of radial location and wall currents, radial current densities and magnetic fields as a function of axial location. Additionally, radial electric field measurements were attempted using short monopole stubs, but plasma sheathing complications rendered those data unusable.

A 30 cm diameter monoenergetic electron beam generated using the Simulation Physics Incorporated SPI 5000 machine was injected axially into the experimental chamber through an aluminized mylar membrane. Suitably gasketed to complete the vacuum tight integrity of the chamber, this transmitting anode of the machine diode formed the entrance plate and allowed the drift chamber to be maintained at a fixed pressure for each shot. The pressure range explored extended from less than one micron to, in some instances, twenty torr. histories of the quantities enumerated above along with electron beam machine diagnostic voltage and current outputs were monitored for each shot on twenty-three separate data channel: (each equalized to 350 MHz bandwidth) and displayed on Tektronix 519 oscilloscopes. The total body of data acquired corresponded to three different mean energies of the injected beam - 40, 60, and 125 keV; two different chamber lengths, 18 and 30 cm; and the pressure range stated above.

Details of the experimental apparatus and techniques are to be found in reference (1). Additional discussion is also presented in Appendix B of this report. This report will present reduced time history and tabular data on selected pressures for the nominal 40 keV mean-energy injected beam. The length of the test chamber was 30 cm and the injected current pulse length was 30 nsec FWHM. Additional similar interim reports will cover the remaining two sets of data comprising the nominal 60 keV mean-energy beam into the 18 cm length chamber and nominal 125 keV beam into the 30 cm length chamber. A final report will contain analyses and correlations of the three data sets covered in the interim reports as well as the 60 keV data set previously reduced and reported on in reference (1). The final report will also contain results of

computer calculations using Kaman Sciences' two-dimensional code EBBTIDE for comparison with appropriate experimentally determined quantities. EBBTIDE provides a self-consistent, fully electromagnetic solution to charged particle electrodynamic problems. Comparisons of EBBTIDE calculations to date have been against electron beam experimental data corresponding to end-on photon illumination of a right circular cylinder and against underground test data of a right circular cylinder enclosing a sphere located on the axis of the cylinder. Results from the three-dimensional code TRIFIC, which uses the same basic algorithms as EBBTIDE, have also been compared against underground test data corresponding to side-on illumination of concentric right circular cylinders. In all cases, agreement has been to within a factor of two in amplitude and waveshape.

The remainder of this report has been organized into four main sections contained in Sections II, III, IV and V. Section II describes the process which has been used to obtain the characterization of the injected electron beam mean energy and current (as a function of time). Section II contains time history waveforms of various data categories. Section IV contains summary tables and plots of selected data from Section III. Finally, Section V discusses the experimental and processing errors inherent in the data of Section III.

## II. CHARACTERIZATION OF THE INJECTED ELECTRON BEAM

A reliable working understanding of the nature of the injected beam is of course crucial in interpreting and applying the experimental results to actual systems situations. Additionally, an accurate specification of the injected beam in terms of energy, current density and angular distribution is required input to any computer code which is intended to simulate IEMP phenomena occurring within the chamber. A detailed comp. Sison of experimental vs computed results using

Kaman's EBBTIDE code is to be presented in the final report on this project. The curves presented in this section will serve to characterize the injected beam in sufficient detail to allow useful interpretation of the experimental results presented within the report.

As is discussed in reference (1)\*, the injected 60 keV electron beam used in generating the data presented therein can be considered quite uniform over its entire diameter. Recent evidence, however, has appeared indicating that under the operating conditions of the SPI PULSE 5000 electron beam machine used to generate shorter pulse, lower energy data such as that presented herein, the injected beam may assume a degree of nonuniformity. This nonuniformity is manifested in a current density distribution in which the beam center is less dense than the beam edge by something on the order of a factor of one half. This circumstance is of critical importance in the context of code comparison against the experimental data and will have to be considered when defining the code input.

Three additional quantities beyond uniformity must be specified in order to fully characterize the injected beam which drives the experiment; beam energy, current density and angular distribution of the injected electrons. Appendix III of reference (1) discusses in detail the considerations and procedures involved in converting the machine diagnostic outputs corresponding to shank voltage and total diode current to the more pertinent quantities of interest, namely, injected beam energy and current density. Briefly, what is required is to correct the machine voltage monitor output for the inductive voltage drop between the monitor itself and the diode gap in

<sup>\*</sup> Reference (1). Duval, J.S., Rich, W.F., and Clarke, C.A. "A Study of IEMP/SGEMP Phenomenology Using Electron Beam Simulation." Kaman Sciences Report (K-74-126U(R), November, 1974.

which the electron beam is generated. With the correction applied, the resultant voltage waveform represents the time history of the accelerating potential applied to the electrons emitted from the diode cathode. At each instant in time, the electrons impinging upon the anode plane have an essentially monoenergetic distribution which corresponds to the potential difference that has accelerated them across the diode gap. In order to arrive finally at the energy distribution of the injected beam, the impinging electron beam must be transported through the .25 mil aluminized mylar diaphram and wire mesh which constitutes the diode gap anode. Reference (1) contains curves generated by the Monte Carlo code EPIC which, when applied to the indicent electron beam, yield mean energy, angular distribution and current density of the beam which is ultimately injected into the test chamber.

Figure 1 presents the "typical" machine voltage monitor waveform associated with the group of data presented in this report. This waveform was constructed by computing the mean and standard deviation values of the individual machine voltage waveforms (calibration factor of 9.8 kv/v) at two nanosecond intervals for each shot in the series included in this report. The center curve represents the mean or the "typical" waveform, while the upper and lower curves represent the  $\pm$   $\sigma$  values.

The inductive voltage correction described above depends upon an  $L \frac{dl}{dr}$  term in which I is the current flowing in the diode circuit, namely the current measured on the machine current monitor (calibration factor of 64 amp/volt). A "typical" machine current waveform was generated in the same manner as described above for machine voltage. Figure 2 presents the resulting curves. The mean curve shown in this figure was implemented in correcting the machine voltage in Figure 1. The curve in Figure 3 represents the resulting diode-gap or electron-accelerating voltage.

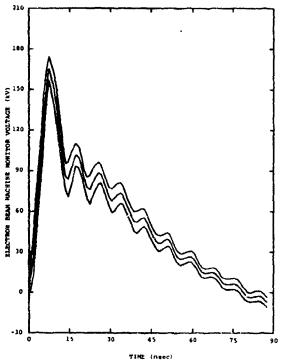


Figure 1. "Typical" machine voltage monitor output. Centar curve is the mean of 14 shots; upper and lower curves are standard deviations.

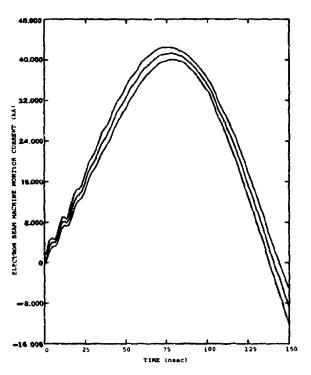


Figure 2. "Typical" machine current monitor output.

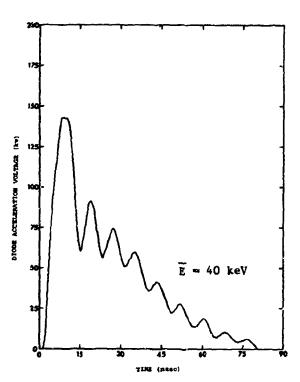


Figure 3. Sleptron beam machine diode gap accelerating voltage.

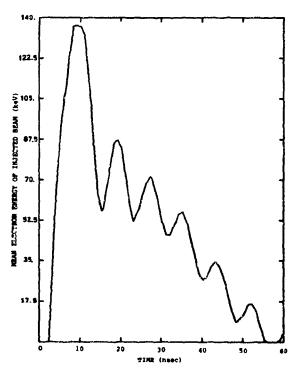


Figure 4. Injected beam electron mean energy corresponding

Figure 4 presents mean injected-beam energy vs time corresponding to the "typical" waveform in Figure 1. This figure can be used to determine the mean energy of the injected beam corresponding to the machine voltage output in Figure 1 for any instant in time.

The second beam quantity of interest is current density. Figure 5 displays the injected beam current measured on a solid aluminum plate 1 cm behind the machine anode plane. (A discussion of the errors in the injected current measurement is to be found on page 172 of reference (1). Recently available data on the injected current suggests that, due to space charge limiting very close to the injection plane, Figure 5 may be in error on the low side.)

## III. PRESENTATION OF DATA

Data acquired using the 40 keV beam described in the previous section included time-correlated and dependent moebius-loop B data, total and spatially-resolved transmitted currents, collected wall currents and localized radial current density. In this section are presented time history curves of data from each of these categories. It should be noted that during processing, the polarities of some of the sets of time history data presented in this section have been inverted. This is, of course, incidental and, once noted, should not cause difficulty in interpretation of the data.

#### Magnetic Fields

Because of the relatively low signal-to-noise ratio inherent in the 40 keV data considerable difficulty was encountered in the processing of the B loop outputs in this data group. In particular, the integration process required in converting the moebius loop output to magnetic fields is quite sensitive to systematic digitizing errors

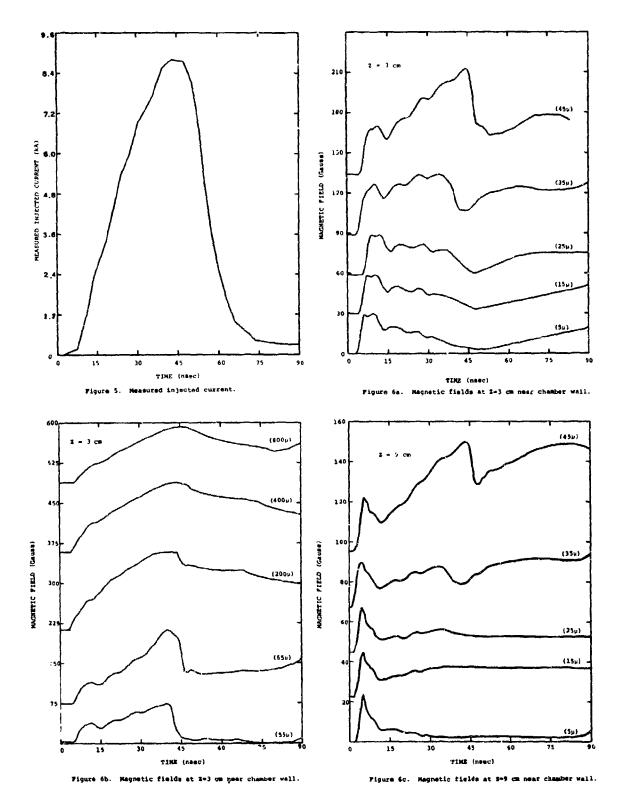
resulting from imprecision in establishing the zero reference as discussed in Section V. This is of course true for all cases, but the problem is compounded from a relative error point of view when the signal amplitudes are small as in this instance. This difficulty is discussed in Section V.

Figures 6a through 6j display magnetic fields obtained over the pressure range of 5 to 800 microns. In these and subsequent figures, the individual curves are displaced vertically simply as a convenience for presentation purposes so that the progression of behavior as a function of pressure is apparent.

## Transmitted Current

The curves in Figures 7a and 7b display the total transmitted currents collected on the solid chamber endplate as a function of time and cavity pressure.

Figures 8a through 8m display the currents detected on each of the individual concentric rings which constitute the chamber endplate. These rings permit resolution of the radial distribution of the transmitted current into five regions. However, the rings can be driven in an antenna mode at times in the presence of high frequency radial electric fields. (See reference (1), p. 183.) Hence in some cases they do not respond as simple current collectors and thus some care is indicated in the interpretation of their output. Table I gives the dimensions of the endplate collection rings, which are approximately equal in area.



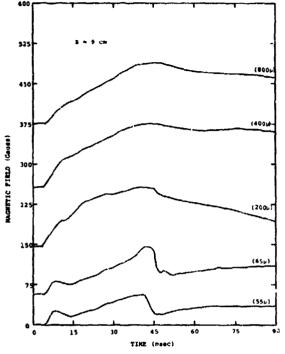


Figure 6d. Magnetic fields at 1-9 cm near chamber wall.

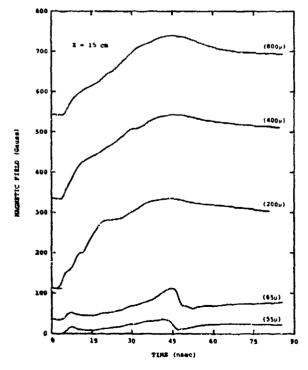
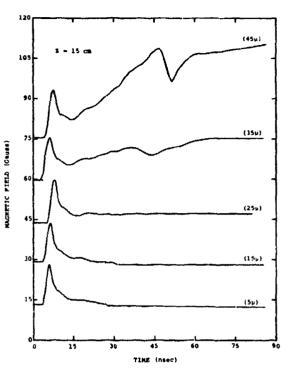


Figure 6f. Regnetic fields at 4-15 cm near chimber wall.



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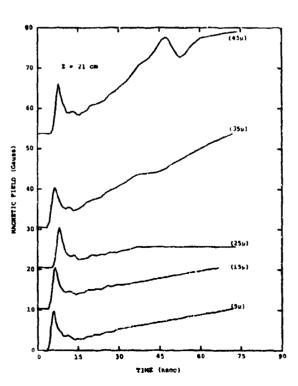


Figure 6q. Magnetic fields at %-21 cm mear chamber well.

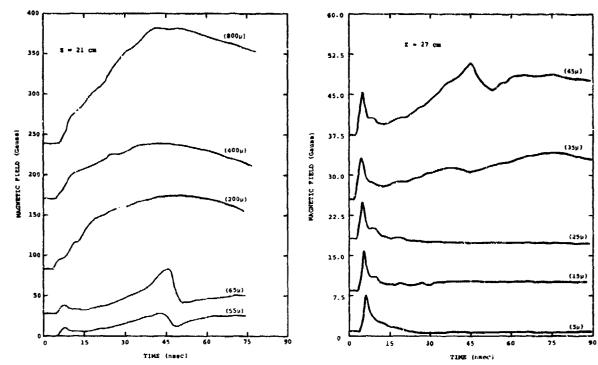


Figure 6h. Magnetic fields at 1=21 cm near chamber wall

Figure 61. Magnetic Sields at 5=27 cm numr chamber wall.

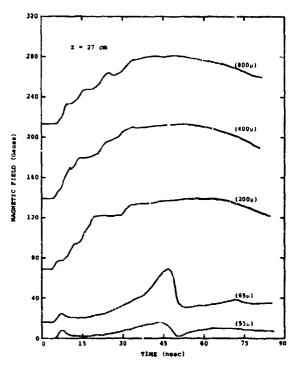


Figure 6j. Regnetic fields at 8-27 on near chamber wall.

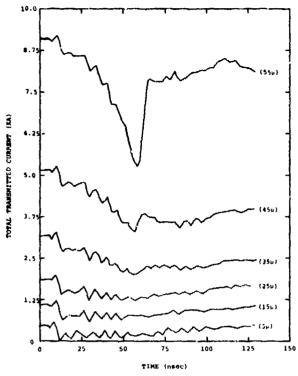


Figure 7s. Total transmitted current measured on solid endplate behind the equal-area rings.

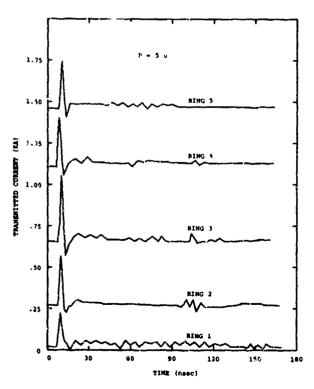


Figure 8a. Transmitted current measured on equaleres rings.

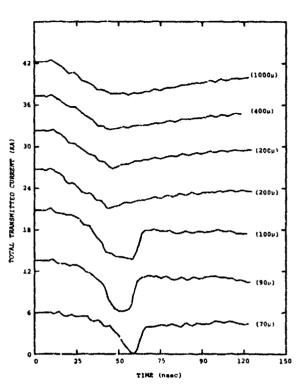


Figure 7b. Total transmitted current measured on solid endplate behind the equal-area rings.

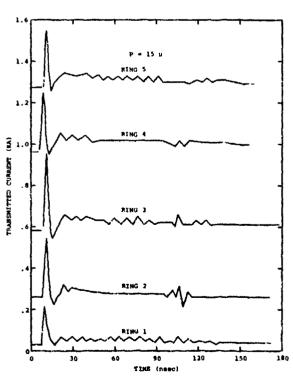


Figure Sb. Transmitted current measured on equalarea rings.

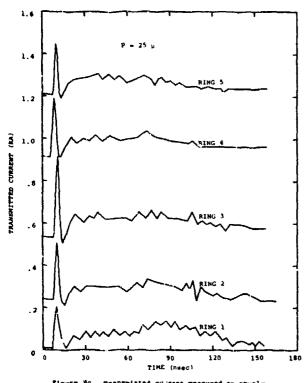


Figure Wc. Transmitted current measured on equalarea ringe.

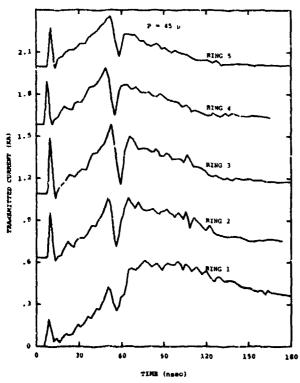


Figure So. Transmitted current measured on equal-

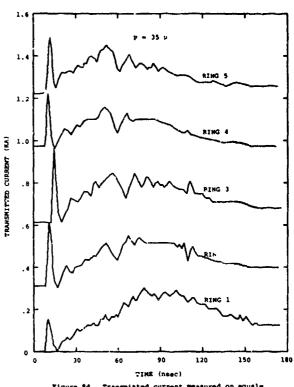


Figure 8d. Transmitted current measured on equaleres rings.

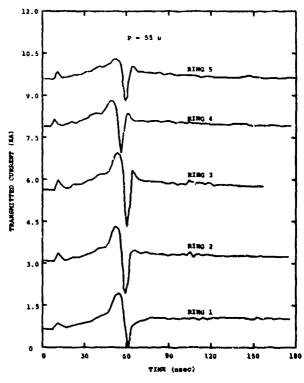


Figure 8f. Transmitted current measured on equalerem rings.

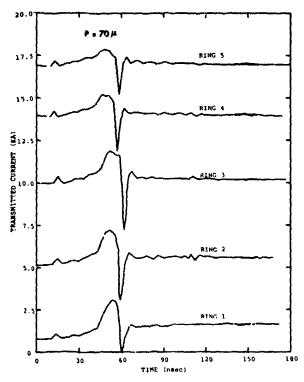


Figure Ag. Transmitted Current measured on equalarea rings.

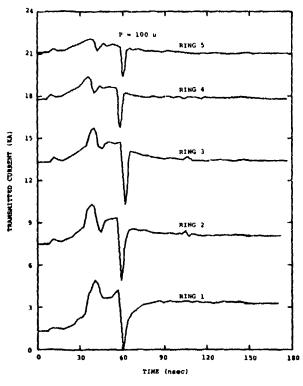


Figure \$1. Transmitted current measured on equalerea rings.

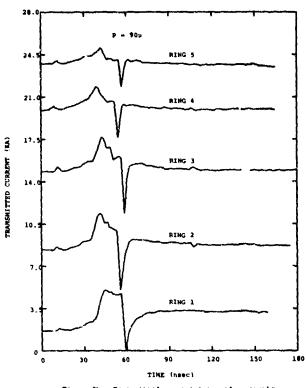
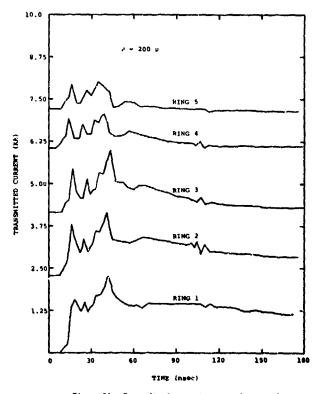
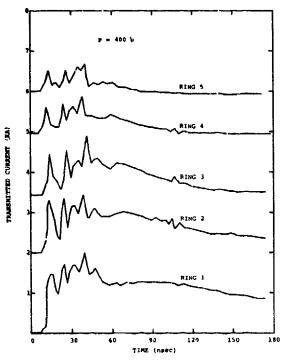


Figure 8h. Transmitted current measured on equalarea rings.



Pigure 8j. Transmitted ourrent measured on equalarea rings.



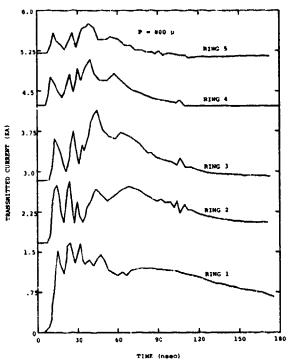


Figure 8x. Transmitted current measured on equalarea rings.

Figure 81. Transmitted current measured on equalarea rings.

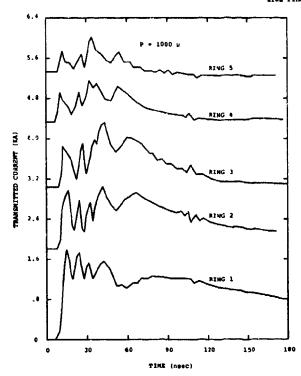


Figure Cm. Transmitted current measured on equalarea rings.

TABLE I. Chamber Endplate Current Ring Geometry

DING NO	RADII (CIL)	
RING NO.	INNER	OUTER
1	<del>1</del>	6.7
2	6.8	9.5
3	9.6	11.7
4	11.8	13.6
5	13.7	15.0

### Collected Wall Currents

The segmented-chamber-body construction of the test chamber described in reference (1) allows the monitoring of total current flowing in the chamber wall at five successive locations down the length of the cavity. The subtraction of the signal developed across the resistive gasket material in one section from that immediately nearer the injection end of the chamber yields the net current collected on the wall segment in question. Thus the average radial currents over 6 cm segments are sampled at five locations down the length of the chamber. Table II summarizes the locations of the various sections. These results are presented in Figures 9a through 9j.

TABLE II. Locations of Wall Segments. 2 = 0 represents the injection plane.

Wall	Channels	Z Location (cm)			
Segment No.	Subtracted	From	То		
1	22A - 15A	0	6		
2	15A - 16A	6	12		
3	16A - 17A	12	18		
4	17A - 18A	18	24		
5	18A - 19A	24	30		
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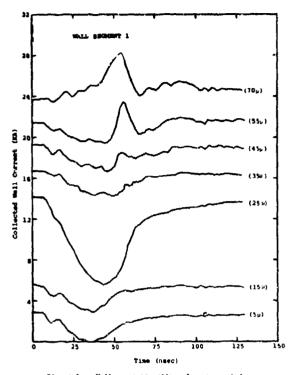


Figure 9s. Wall currents collected on segmentedchamber elements.

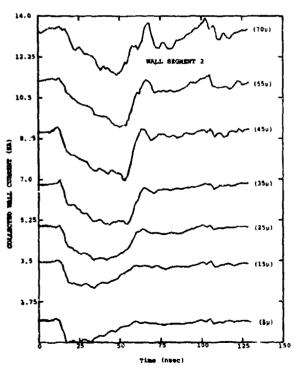


Figure Sc. Wall currents collected on segmentedchamber elements.

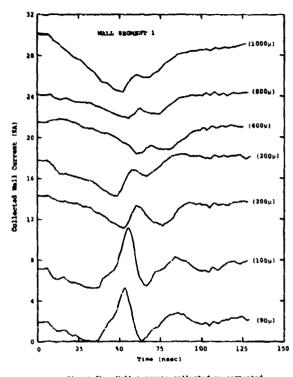


Figure 9b. Wall currents collected on segmentedchamber elements.

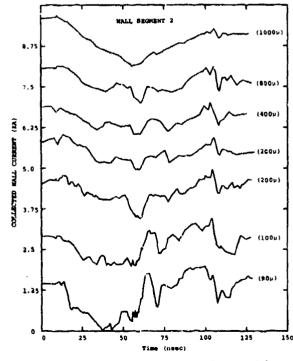


Figure 9d. Wall currents col? metad on segmentsdchamber elements.

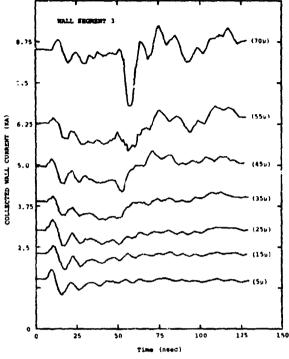


Figure 5e. Wall currents collected on segmented-

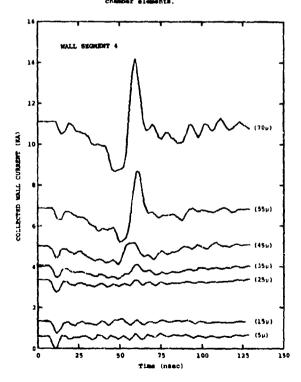


Figure 9g. Wall currents collected on segmentedchamber elements.

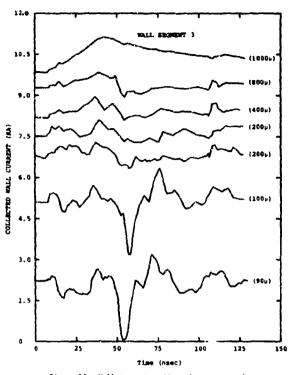


Figure 9f. Well currents collected on segmentedchamber elements.

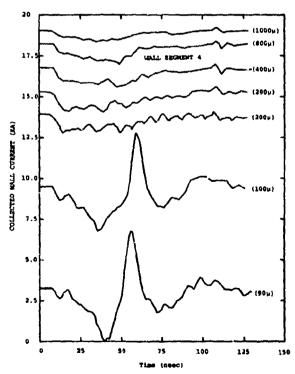
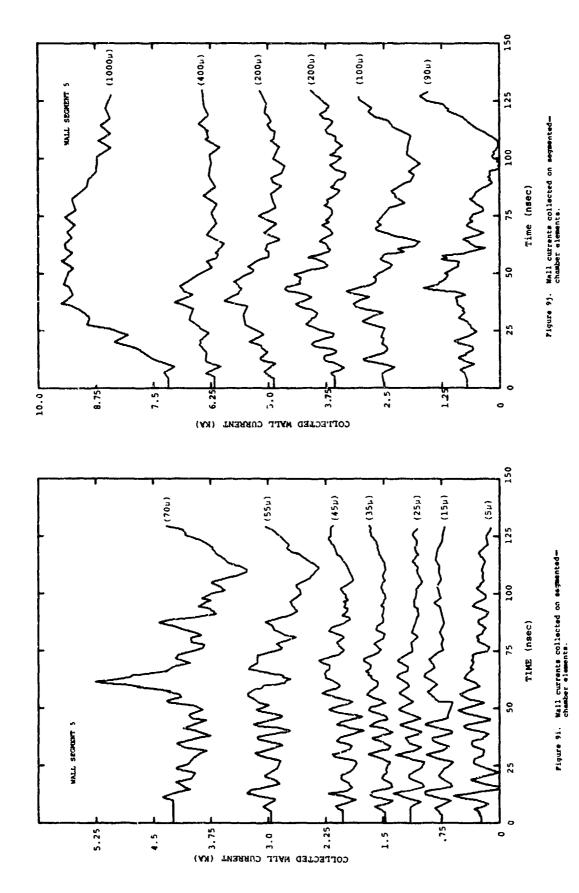


Figure 9h. Wail currents collected on segmentedchamber elements.



#### Radial Current Densities

An additional set of measurements were performed in the 40 keV sequence. These consisted of sampling the radial currents at seven localized points by means of flush-mounted current probes (FMCP) mounted in the chamber wall. Since these probes were employed only in the 40 keV shot sequence, a discussion of the probe construction and response is included in this report as an Appendix. The response analysis discussed therein indicates that the FMCP is an excellent device for sampling the impinging current densities. Figures 10a through 10j present data obtained using these sensors. We have elected to display these data on the same time scales as the wall segment currents to facilitate comparison of their wave shapes.

## IV. PEAK VALUES

Figure 11 displays peak magnetic field values measured at Z=3, 15 and 27 cm, that is, near the entrance, middle and end of the drift chamber. These data are plotted as a function of pressure.

Figure 12 similarly presents the peak values of total transmitted current against pressure. In Figure 13 are curves of collected wall current peak values for chamber sections near the front, middle and rear of the test chamber.

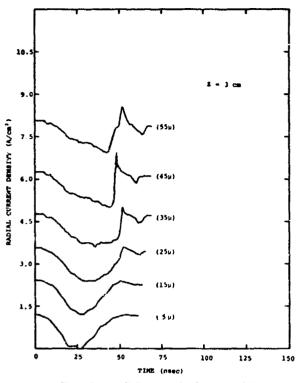


Figure 10s. Radial current Gensity measured by the flush-mounted current probes (FMCF).

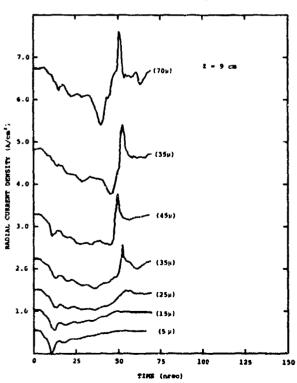


Figure 10c. Radial current density measured by the flush-mounted current probes (FMCF).

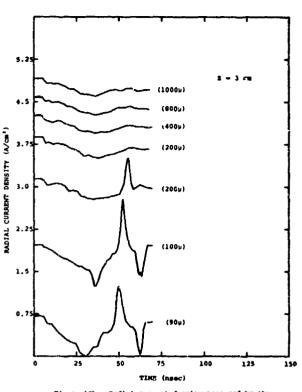


Figure 10b. Radial current density measured by the flush-mounted current probes (FMCP).

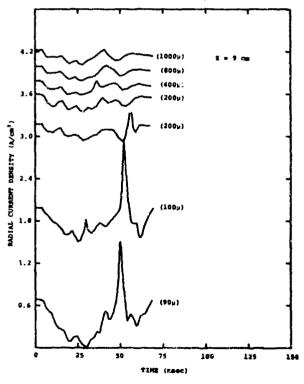


Figure 186. Radiel current density measured by the flush-mounted current probes (FMCF).

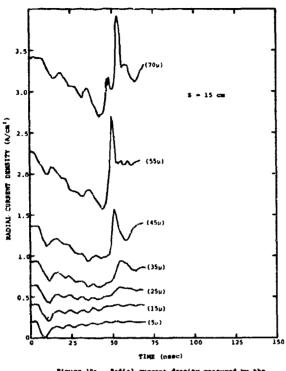


Figure 10s. Radial current density measured by the flush-mounted current probes (FMCP).

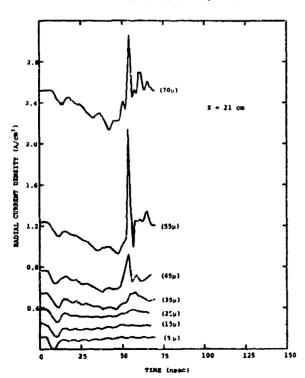


Figure 10g. Radial current density measured by the flush-mounted current probes (FMCF).

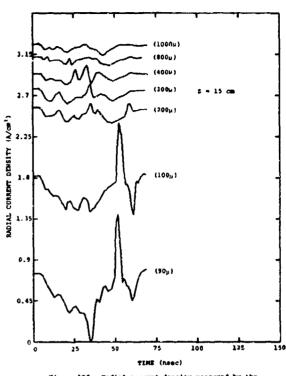


Figure 10f. Radial current density measured by the flush-mounted current probes (PMCF).

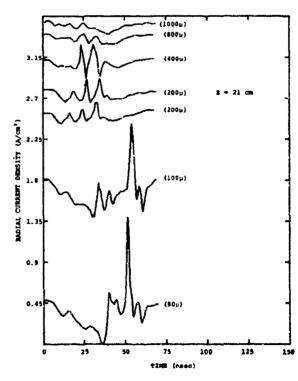


Figure 10h. Radial current density measured by the flueb-mounted current probes (FMCP).

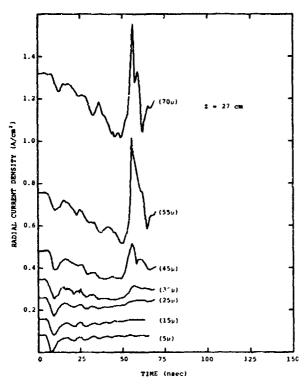


Figure 10: Radial current density measured by the flush-mounted current probes (FMCP).

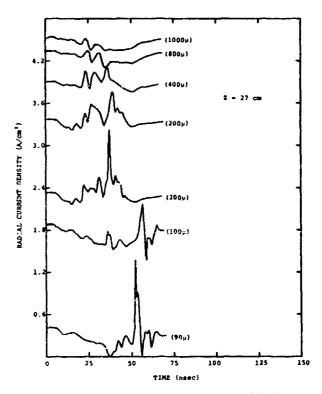


Figure 10j. Radial current density measured by the flush-mounted current probes (FMCP).

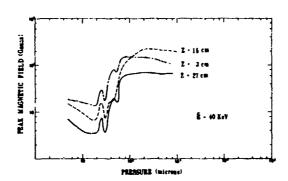


Figure 11. Peak magnetic fields we pressure near front, middle and rear of chamber.

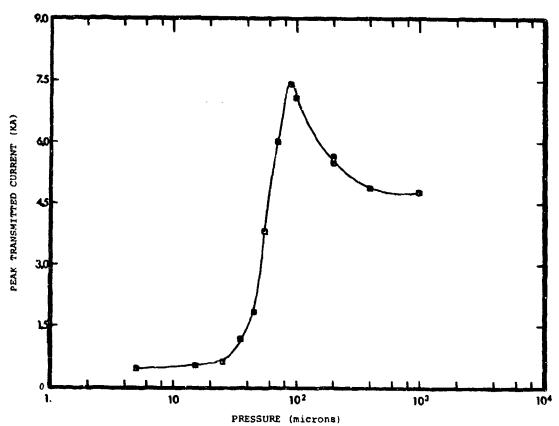


Figure 12. Peak Transmitted current vs pressure.

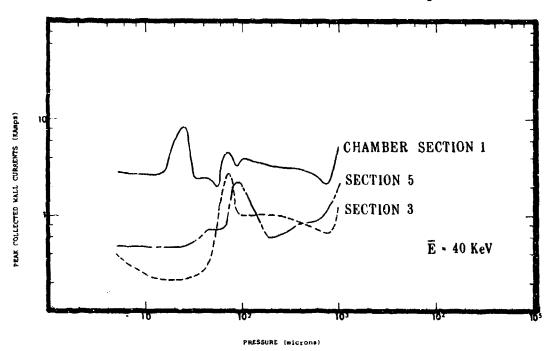


Figure 13. Peak collected wall currents near front, middle and rear of chamber

Table III summarizes the transmitted current distributions as obtained from the peak values of collected current on each of the individual endplate rings.

TABLE III. Peak currents on endplate collector rings.

	Peak Current (kA)				
Pressure (μ)	Ring l	Ring 2	Ring 3	Ring 4	Ring 5
5	.03	.02	.04	.04	.03
10	.05	.04	.05	.05	.05
15	.03	.04	.04	.06	.06
20	.07	.06	.07	.07	.07
25	*	.06	.05	.06	.05
30	.12	.09	.10	.09	.09
35	.15	.13	.13	.09	.12
45	.56	.39	.36	.30	28
55	.52	.41	.44	.35	.28
65	1.31	1.16	1.19	.88	.79
200	2.54	1.92	1.67	.91	.73
400	2.31	1.60	1.39	.98	.74
800	1.81	1.28	1.12	.76	.58

<sup>\*</sup> Bad data film.

## V. ERROR ANALYSIS

#### General Considerations

Sources of error have been divided into three categories: experimental error, trace digitization error and propagation of these two error types in subsequent processing. The third area of concern deals with the sensitivity of the final results to inaccuracies in the input data.

Conversion of Oscilloscope Traces to Volts vs Time

In order to set the time scale on each scope, a sine wave of known frequency was recorded on each channel photograph prior to each shot. The distance (from an arbitrary zero point) to each successive peak of this waveform was digitized. From these data the mean  $\mu$  and standard deviation  $\sigma$  of the distances  $x_{i+1}$ - $x_i$ ,  $i=1, 2, \ldots$ , n between successive peaks were computed.

Let X be the random variable associated with distance errors in the digitized x (time) axis. We assume that X has mean 0 and variance  $\sigma^2$ . Let  $\mu$  be the "actual" sine wave inter-peak distance, then  $X_i$  will be distributed as  $X + i\mu$ . Hence  $X_{i+1} - X_i$  will have mean  $\mu$  and variance  $2\sigma^2$  given independence of  $X_i$  and  $X_{i+1}$ .

The statistic  $\mu$  was used to estimate  $\mu$  and  $\frac{\sigma}{\sqrt{2}}$  was used to estimate  $\sigma$ .  $\sigma$  was found to be less than .036 mm on nearly every shot. Other sources of error, such as non-uniformity of the sine wave, have been ignored. These sources would cause a slight under-estimate of data quality rather than an over-estimate. It is assumed that

voltage errors (vertical distances) are distributed the same as time errors (horizontal distances).

Voltage values are calculated from the raw digitized data as:

$$v = \frac{\left(d - d_{o}\right)a}{m} s$$

where:

d is the vertical coordinate of the trace on the film (mm)

d is the vertical coordinate cooresponding to 0 (mm)

m is an optical magnification factor associated with the digitizing process

a is signal attenuation, and

s is scope sensitivity  $\left(\frac{v}{mm}\right)$  .

Relativising voltage errors  $\Delta V$  to the peak voltage encountered  $\left|V\right|_{\text{max}}$  , one obtains

$$\sigma\left(\frac{\Delta V}{|V|_{max}}\right) = \sqrt{\sigma^2\left(\frac{\Delta (d-d_o)}{|d-d_o|_{max}}\right) + \sigma^2\left(\frac{\Delta a}{a}\right) + \sigma^2\left(\frac{\Delta s}{s}\right) + \sigma^2\left(\frac{\Delta m}{m}\right)}.$$

 $\sigma\left(\Delta\left(d-d_{_{\mathrm{O}}}\right)\right)$  was approximated by .036 mm (see above) and  $\left|d-d_{_{\mathrm{O}}}\right|_{\mathrm{max}}$  was tabulated for a sample of curves from each type of data.

In all curves investigated

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$$\sigma\left(\frac{\Delta(d-d_o)}{|d-d_o|_{man}}\right) < 5.5%$$

Other values assigned were:

$$\sigma\left(\frac{\Delta a}{a}\right) = 18$$

$$\sigma\left(\frac{\Delta s}{s}\right) = 28$$

$$\sigma\left(\frac{\Delta m}{m}\right) = .058$$

Hence  $\sigma\left(\frac{\Delta V}{|V|_{max}}\right)\approx 6\%$  which represents the error inherent in the digitized data upon which all further processing was performed.

Transmitted Current Measurements (Total and Radially Resolved)

These measurements result from measuring voltages developed across resistive shunts and therefore involve application of Ohm's Law in the form I = V/R. Percentage errors associated with peak values were evaluated according to the following procedures.

Letting  $\Delta I$ ,  $\Delta V$  and  $\Delta R$  denote random variables corresponding to current, voltage and resistance errors respectively with variances  $\sigma^2(\Delta I)$ ,  $\sigma^2(\Delta V)$  and  $\sigma^2(\Delta R)$ , one obtains

$$\sigma\left(\frac{\Delta I}{|I|_{max}}\right) \cong \sqrt{\sigma^2\left(\frac{\Delta V}{|V|_{max}}\right) + \sigma^2\left(\frac{\Delta R}{R}\right)}$$

As determined in the preceeding section,  $\sigma\left(\frac{\Delta V}{|V|_{max}}\right) = .06$ . The worst case  $\sigma\left(\frac{\Delta R}{R}\right)$  for the channels under consideration in this section was about .05. Hence  $\sigma\left(\frac{\Delta I}{|I|_{max}}\right) < 8\%$  for the total transmitted current measurements. Recent considerations relative to interpretation of the current collection ring data, however, has indicated that the response of these rings is not well understood. The antenna mode response of the concentric ring configuration appears to be greater than originally determined. It is not possible at this time, therefore, to complete the error analysis of those sensors.

# Wall Segment Currents

The net wall current in each of the five sections comprising the body of the drift chamber is computed as  $v_2(t)/r_2 - v_1(t)/r_1$  where  $v_1(t)$  and  $v_2(t)$  are the digitized voltages associated with two successive sections and  $r_1$  and  $r_2$  are the corresponding gasket resistances. The error analysis here is complicated by the fact that relative timing discrepancies between the two voltage waveforms must be accounted for.

Timing errors in a given trace are assumed to be of two kinds. The first is a systematic error. That is, due to inaccurate determination of the timing zero point, the entire waveform is shifted in time with respect to true zero and hence with respect to the waveform with which it is to be differenced. The second error source is a random inaccuracy in the determination of the time of each individual data point. It was judged that these random errors were quite small leaving the systematic error of the first type dominant.

To analyse the effect of the systematic timing errors, let  $i_1(t)$  and  $i_2(t)$  be correct current values whose difference  $i_2(t) - i_1(t)$  is desired. Due to errors of various sorts,  $i_2(t)$  is obtained instead of  $i_2(t)$  and  $i_1(t)$  instead of  $i_1(t)$ . Allow a relative time shift error of  $i_1(t)$  are assume that there exist time shifts  $i_1(t)$  and  $i_2(t)$  such that  $i_1(t)$  and  $i_1(t)$  are small amount  $i_1(t)$  and  $i_1(t)$  are  $i_1(t)$  and  $i_1(t)$  and  $i_1(t)$  are  $i_1(t)$  and  $i_1(t)$  are i

The difference between the calculated value and the desired result  $i_2(t)$  -  $i_1(t)$  is of interest. The triangle inequality yields:

$$\begin{aligned} &|i_{2}(t)-i_{1}(t)-(i_{2}(t)-i_{1}(t))| \\ \leq &|i_{2}(t)-i_{2}(S_{2}+t)|+|i_{2}(S_{2}+t)-i_{2}(t)|+|i_{1}(t)-i_{1}(S_{1}+t)|+|i_{1}(S_{1}+t)-i_{1}(t)| \\ \leq &b_{2}(t)+\varepsilon_{2}+b_{1}(t)+\varepsilon_{1} \end{aligned}$$

The bound  $b_k(t)$  measures the local variation in  $i_k'(t)$  and will vary with t. In simplest terms, small time shifts will cause dramatic changes in  $i_k'(t)$  where  $b_k(t)$  is large and  $i_k'(t)$  has steep slopes.

In a number of cases including high and low pressures,  $b_k(t)$  was computed for a = 2.5 ns, k = 1, 2 and t corresponding to the maximum of  $|i_2(t)-i_1(t)|$ .  $b_1(t)+b_2(t)$  was found to be less than 0.7 kA in nearly every case. Assigning standard deviations of 0.4 kA to  $\epsilon_1$  and  $\epsilon_2$  one obtains a standard deviation of 0.9 kA for the total error. The estimate is believed to be conservative in the sense that it bounds the true standard deviation but that 0.6 kA is probably a more realistic estimate.

# Magnetic Fields

The magnetic field results were calculated from the moebius loop data using the formula:

$$B(t) = \frac{L}{2AR} \left\{ v(t) + \frac{R}{L} \int_{0}^{t} v(\tau) d\tau \right\}$$

where:

 $A = (1.08 \pm .01) \times 10^{-4} m^2$ 

 $R = 25\Omega$ 

 $L = (16.9 \pm .01) \times 10^{-9} hy$ 

v(t) is the digitized voltage trace corrected for data channel attenuations. That is, v(t) represents the output voltage of the sensor itself. The presence of errors in v(t) can be handled by replacing v(t) with  $v(t)+\epsilon(t)$  where  $\epsilon(t)$  is an error term. Define

$$B^{*}(t) = \frac{L}{2AR} \left\{ v(t) + \varepsilon(t) + \frac{R}{L} \int_{0}^{t} \left( v(\tau) + \varepsilon(\tau) \right) d\tau \right\}$$

Hence, 
$$|B^*(t)-B(t)| = \left| \frac{L}{2AR} \left\{ \varepsilon(t) + \frac{R}{L} \int_{0}^{t} \varepsilon(\tau) d\tau \right\} \right|$$

$$= \leq \frac{L|\varepsilon(t)|}{2AR} + \left| \frac{1}{2A} \int_{0}^{t} \varepsilon(\tau) d\tau \right|$$

$$\leq \frac{L|\varepsilon(t)|}{2AR} + \frac{t}{2A} \max_{0 \leq \tau \leq t} |\varepsilon(\tau)|$$

Because errors of a small level shift and/or rotation are judged present in the process of reading the photographic images, one must allow for cumulative error rather than assuming that the error will "average out" over time. This cumulative error corresponds to the term:

$$\frac{1}{2A}\int_{C}^{t}\varepsilon(\tau)d\tau$$

The following example illustrates the problem of cumulative error. Given a uniform level shift error in v(t) of 2% of its peak value, a simple computation shows that

$$\frac{1}{2A}\int_{0}^{t}\varepsilon(\tau)d\tau$$

could accumulate an error equal to the peak value of  $\frac{Lv(t)}{2AR}$  in time  $t = \left(\frac{1}{.02}\right) \frac{L}{R} \approx 34$  ns. At t = 34 ns it would not be uncommon to find values of B\*(t) of roughly this same magnitude.

In summary, the values calculated for B(t) decrease in accuracy with advancing time and can be rather unreliable even at times as early as 35 ns. The values for B(t) at times near zero approach the accuracy of the digitized voltages since the errors in A, R and L are small.

What this means in practice for this set of data in which both the signal levels are small and pulse durations are short is that in those magnetic fields for which the peak values occur beyond 40 nsec, the peak values are not very reliable. It is estimated that a bound on the error on the computed value of the B fields is probably between 50 and 75% at 40 nsec. There is evidence, however, that the error is not nearly that bad in much of the data; but quantifying it in each case is extremely difficult. One reason for believing the error is much less is that on many shots in which there are three loops azimuthally distributed at given Z coordinate, the resulting calculated B fields agree to within 15%. In other cases the disagreement is marked, and a late time ramp attributable to a fixed zero offset in the raw data is apparent.

Attempts to simply subtract out the associated zero were not satisfactory and it was felt that further tinkering with the data to produce better "agreement" was scientifically unwarranted.

It should be noted that the 60 and 125 keV data sets have much less error associated with them. This is due to two factors. First those data have significantly better signal-to-noise characteristics in that the signals are of both greater amplitude and longer pulse duration. Secondly, the digitizing of those data was performed using much more accurate equipment and processes than the present set.

## Flush-Mounted Current Probes

The formula  $J_r(t) = K_1 v(t) + K_2 \frac{dv(t)}{dt}$  was used to calculate the radial current densities from the flush-mounted current probe voltage data with  $K_1 = 129.9$  and  $K_2 = 158.4$ . (See Appendix.) The derivative  $\frac{dv}{dt}$  at  $t_2$  was approximated by evaluating the slope of a parabola passing through  $(t_1, v(t_1))$ ,  $(t_2, v(t_2))$  and  $(t_3, v(t_3))$  where  $t_1$ ,  $t_2$  and  $t_3$  are consecutive time points. A new parabola was fit to successive sets of three points advancing along the data points one at a time.

Here the sensitivity of the derivative calculation to errors in the input data is of over-riding concern. The result  $J_r(t)$  is least sensitive to errors in v(t) when either the term  $\frac{dv}{dt}$  is small or the term  $K_2\frac{dv}{dt}(t)$  is at least small with respect to the term  $K_1v(t)$ .

In order to evaluate the sensitivity of the derivative calculation to errors in the input times, the derivative was written as a function  $g(t_1,t_2,t_3,v_1,v_2,v_3)$  and the gradient  $\nabla g$  was computed for actual data points. For the most part the standard deviations of the timing errors were approximately 0.25 nsec. It was found that times near the steepest part of v(t) could yield errors exceeding 20% of the resulting  $J_r(t)$  peak value even though the time error  $(\Delta t_1, \Delta t_2, \Delta t_3)$  satisfied the requirement  $((\Delta t_1)^2 + (\Delta t_2)^2 + (\Delta t_3)^2)^{\frac{1}{2}} < 0.25$  nsec. The derivative computation is a good deal less sensitive to errors in v(t) where v(t) is steep. At times when the curve v(t) flattens out, the accuracy of the  $J_r(t)$  values approaches the accuracy of v(t).

In summary, the flush-mounted current probe data has an error bound of about 20% but is probably routinely good to 10%.

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### APPENDIX A

2

### FLUSH-MOUNTED CURRENT PROBE

The flush-mounted current probes (FMCP) employed in this experiment were designed to measure the radial electron current density impinging on localized areas of the test chamber walls. The probes themselves consist of a current collection element which was a rod of diameter 7 mm insulated from its surrounding support structure by a 1.05 mm layer of epoxy. The entire probe assembly was inserted into the wall structure of the chamber so that the face of the probe was flush with the inside wall of the chamber and the support structure and chamber walls were common. Terminals on the collection element and the support structure provide the signal path to a 50 ohm terminated line leading directly to a Tektronix 519 oscilloscope.

There are two potential modes of excitation of the sensor which have been analysed: direct current collection of the radial component of the electron current impinging on the sensor face (the desired response) and the antenna response due to the axial component of the electric field in the vicinity of the sensor. An additional excitation mode is due to displacement currents in the vicinity of the sensor; but this mechanism is judged to be negligible and was not explicitly considered. An analysis of the probe response has been performed assuming ramp functions of appropriate slopes for the  $\mathbf{E}_{\mathbf{Z}}$  and  $\mathbf{J}_{\mathbf{T}}$  driving functions based on the equivalent circuit model for the probe and its 50 ohm load shown in Figure 1-A.

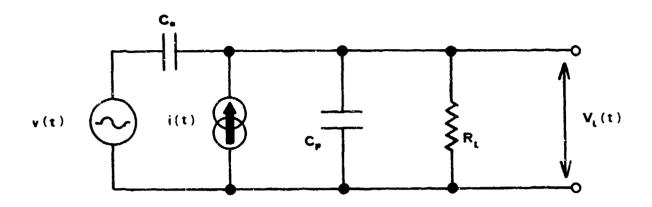


Figure 1-A. Equivalent circuit model of the flush mounted current probe.

In this Figure, v(t) represents the antenna voltage, Ca the antenna capacitance, i(t) represents the collection current on the center rod,  $C_{\mathbf{p}}$  the capacitance formed by the current collection electrode and the rest of the support structure,  $R_{T_{\rm c}}$  is the 50 ohm load and  $V_{T_{\rm c}}$  is the measured voltage output of the probe system. The driving ramp functions were chosen to have slopes similar to the rise times of  $J_r$  and  $E_z$  observed in the experiment. Table 1 tabulates the analysis results.  $V_a$  is the response voltage at the load due to the antenna effects of the probe, V is that due to the impinging current and V is the total response. The table indicates that for times as early as 1 nsec, the error in attributing the entire response to the collected current is less than 3%. At later times the error becomes totally negligible. Therefore, the equivalent circuit may be simplified even further to that shown in Figure 2-A the circuit equation of which is

TABLE 1. Tabulation of Flush-Mounted Current Probe (FMCP) Analysis Results

t(ns)	V <sub>a</sub> (volts)	V <sub>c</sub> (volts)	V <sub>L</sub> (t)(volts)	$\left  \frac{V_a(t)}{V(t)} \right  $
0.2 0.4 0.6 1.0 2.0 4.0 6.0 10.0	.187 .212 .215 .216 .216 .216 .216	0.976 2.570 4.31 7.7 16.3 33.5 50.7	1.163 2.782 4.526 7.9 16.5 33.7 50.9 85.3	16.8 7.7 4.8 2.7 1.3 0.6 0.4 0.2

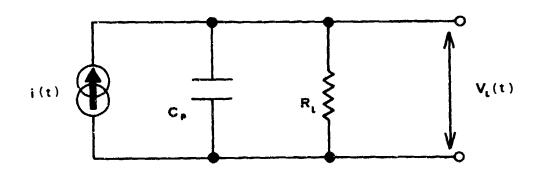


Figure 2-A. Reduced model of the flush-mounted current probe.

$$i(t) = C_p \frac{dV_L}{dt} + \frac{V_L}{R}$$

from which

$$J_r(t) = \frac{C}{A} \frac{dV_L}{dt} + \frac{V_L}{RA}$$

where A = area of the probe collection element.

Hence, inserting the proper numerical values:

$$J_r(t) = 155.8 \frac{dV_L}{dt} + 129.9 V_L$$

where  $J_r(t)$  is given in  $A/m^2$ .

### APPENDIX B

### INSTRUMENTATION DETAILS

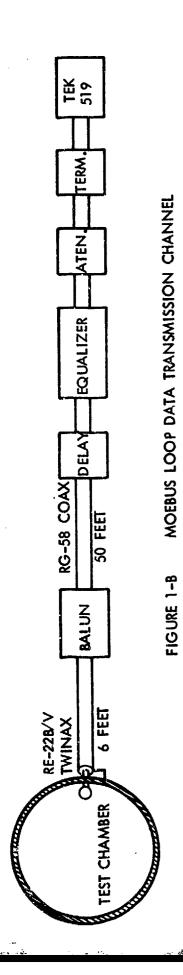
In this section some additional details of the instrumentation of the test chamber not included in reference 1 are presented.

# Magnetic Field Sensors

Standard moebius strip loops with potted gaps were employed as the magnetic field sensors. A good discussion of the principles of operation of the loops themselves can be found in the AFWL EMP Sensor and Simulation Note Number 7. Figure 1-B shows the data channel configuration, while Figure 2-B presents the schematic details of the balun employed. Figure 3-B is a photograph of the sensor itself. Figure 3 of reference 1 shows the loops mounted in the drift chamber walls.

# Current Collection Sensors

Voltage signals proportional to current through the resistive gasket material separating the individual chamber segments were picked off directly by attaching  $50\Omega$  RG-58 cables to the chamber segment flanges. Figure 4-B illustrates this. equal area current rings were isolated from the solid endplate also by resistive gaskets, and the voltage signals developed by collected current on each of those was similarly tapped. Resistances of each gasket were experimentally determined (reference 1, p. 18). Each ring had a signal pickup feedthrough which protruded through the chamber endplate. signals were fed directly down the long  $50\Omega$  cables to the instrument vans where they passed through cable equalizers, delays, attenuators and terminations to the oscilloscopes. All intervening components were of course properly matched so that, from the point of view of the sensor input, the effective load was simply  $50\Omega$ .



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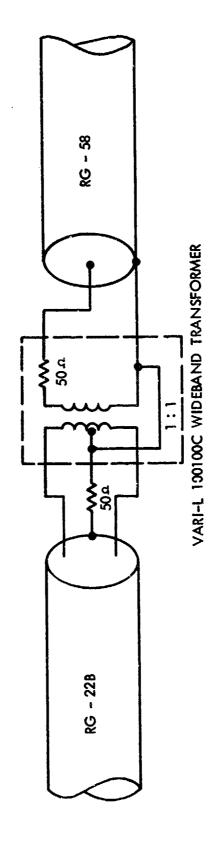


FIGURE 2-B BALUN TERMINATION ELECTRICAL SCHEMATIC



Figure 3-B. Moebius loop magnetic field sensor.

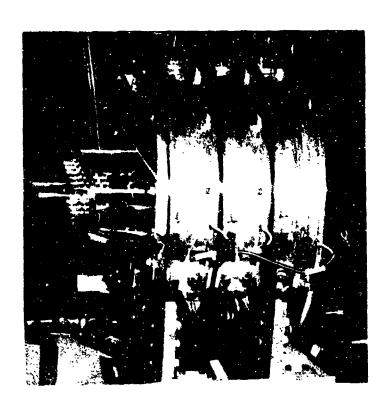


Figure 4-B. External connections of wall segment signal pickups.

# Flush-Mounted Current Probes

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The flush-mounted probes for measuring the radial current density are discussed in Appendix A. Figure 5-B is a photograph of one of the sensors. The output was tapped by direct connection of a  $50\Omega$  cable to two screw terminals on the back of the sensor mount itself. This signal was fed down the cable to the instrument van where it passed through components similar to those discussed in the previous paragraph for the current collection sensors. The effective load on each flush-mounted probe was  $50\Omega$ .

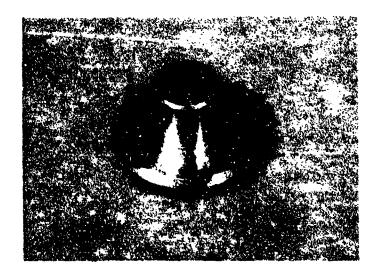


Figure 5-B. Photograph of sensor.

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